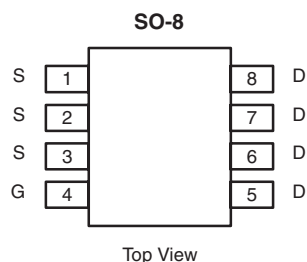


N-Channel 30-V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^a	Q_g (Typ.)
30	0.0085 at $V_{GS} = 10$ V	18	11.7 nC
	0.0125 at $V_{GS} = 4.5$ V	15	

SCHOTTKY AND BODY DIODE PRODUCT SUMMARY		
V_{DS} (V)	V_{SD} (V) Diode Forward Voltage	I_S (A)
30	0.4 at 2 A	5 ^a



Ordering Information: Si4322DY-T1-E3 (Lead (Pb)-free)
Si4322DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

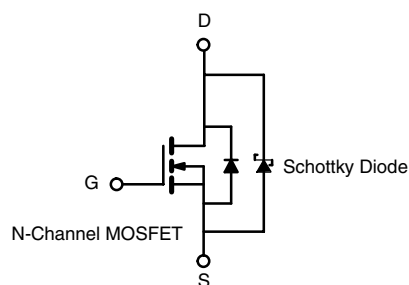
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested

APPLICATIONS

- Synchronous Buck-Low Side
 - Notebook
 - Server
 - Workstation
- Synchronous Rectifier-POL



RoHS
COMPLIANT
HALOGEN
FREE
Available



ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current ($T_J = 150$ °C)	$T_C = 25$ °C	I_D	18	A
	$T_C = 70$ °C		15	
	$T_A = 25$ °C		14 ^{b, c}	
	$T_A = 70$ °C		11 ^{b, c}	
Pulsed Drain Current		I_{DM}	50	
Continuous Source-Drain Diode Current	$T_C = 25$ °C	I_S	5	W
	$T_A = 25$ °C		2.8 ^{b, c}	
Maximum Power Dissipation	$T_C = 25$ °C	P_D	5.4	
	$T_C = 70$ °C		3.4	
	$T_A = 25$ °C		3.1 ^{b, c}	
	$T_A = 70$ °C		2.0 ^{b, c}	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS				
Parameter		Symbol	Typ.	Max.
Maximum Junction-to-Ambient ^{b, d}	$t \leq 10$ s	R_{thJA}	34	40
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	17	23

Notes:

- Based on $T_C = 25$ °C.
- Surface Mounted on 1" x 1" FR4 board.
- $t = 10$ s.
- Maximum under Steady State conditions is 85 °C/W.

SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	30			V
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	1.5		3.0	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{ V}$, $V_{GS} = 0\text{ V}$		0.18	1	mA
		$V_{DS} = 30\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 100\text{ }^{\circ}\text{C}$		22	100	
On -State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}$, $V_{GS} = 10\text{ V}$	30			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 15\text{ A}$		0.007	0.0085	Ω
		$V_{GS} = 4.5\text{ V}$, $I_D = 12\text{ A}$		0.0095	0.012	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}$, $I_D = 15\text{ A}$		56		S
Dynamic ^b						
Input Capacitance	C_{iss}	$V_{DS} = 15\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$		1640		pF
Output Capacitance	C_{oss}			380		
Reverse Transfer Capacitance	C_{rss}			118		
Total Gate Charge	Q_g	$V_{DS} = 15\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 15\text{ A}$		25.5	38	nC
		$V_{DS} = 15\text{ V}$, $V_{GS} = 4.5\text{ V}$, $I_D = 15\text{ A}$		11.7	17.5	
Q_{gs}			5.1			
Q_{gd}			3.6			
Gate Resistance	R_g	$f = 1\text{ MHz}$		2.3	3.5	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}$, $R_L = 3\text{ }\Omega$ $I_D \equiv 5\text{ A}$, $V_{GEN} = 4.5\text{ V}$, $R_G = 1\text{ }\Omega$		24	36	ns
Rise Time	t_r			84	126	
Turn-Off Delay Time	$t_{d(off)}$			36	54	
Fall Time	t_f			17	26	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}$, $R_L = 3\text{ }\Omega$ $I_D \equiv 5\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_G = 1\text{ }\Omega$		12	18	
Rise Time	t_r			36	54	
Turn-Off Delay Time	$t_{d(off)}$			36	54	
Fall Time	t_f			7	11	
Drain-Source Body Diode and Schottky Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^{\circ}\text{C}$			5	A
Pulse Diode Forward Current ^a	I_{SM}				50	
Body Diode Voltage	V_{SD}	$I_S = 2\text{ A}$		0.35	0.4	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 4\text{ A}$, $dI/dt = 100\text{ A}/\mu\text{s}$, $T_J = 25\text{ }^{\circ}\text{C}$		26	40	ns
Body Diode Reverse Recovery Charge	Q_{rr}			16	25	nC
Reverse Recovery Fall Time	t_a			12.5		ns
Reverse Recovery Rise Time	t_b			13.5		

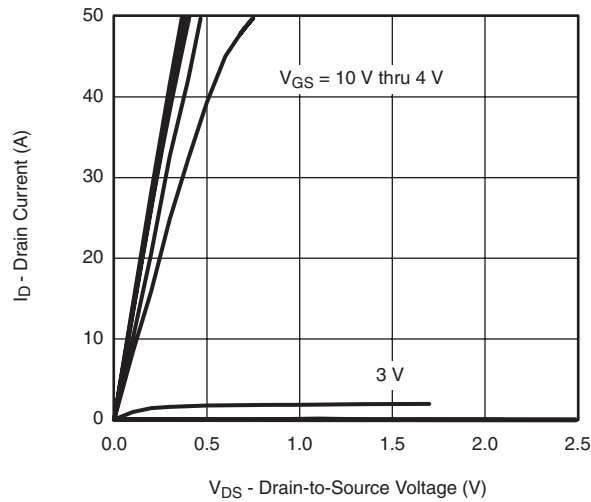
Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
b. Guaranteed by design, not subject to production testing.

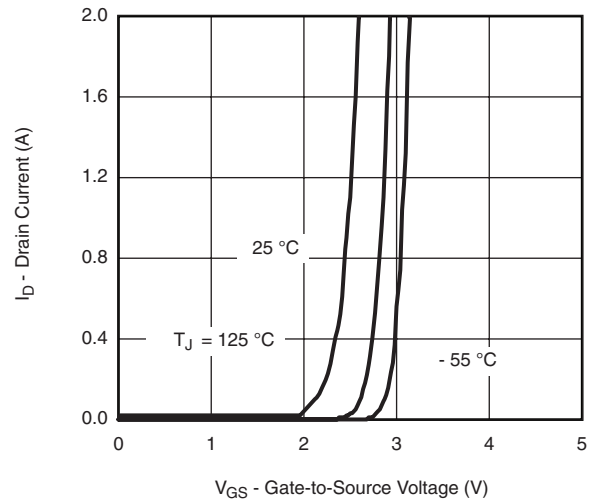
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



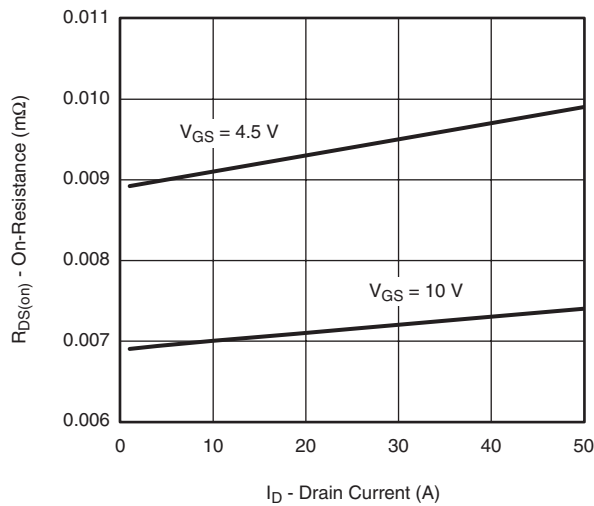
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



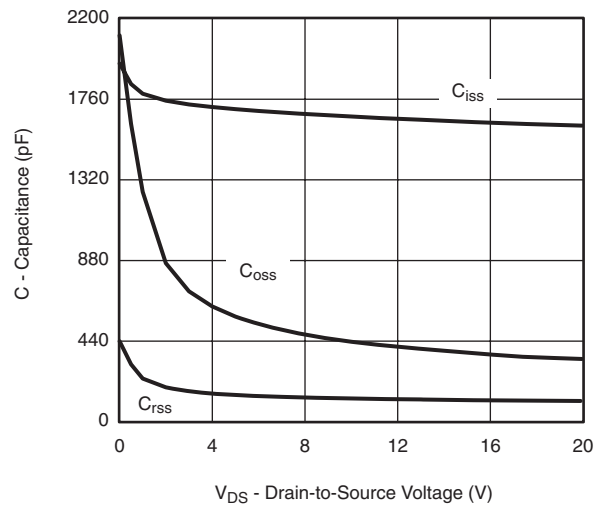
Output Characteristics



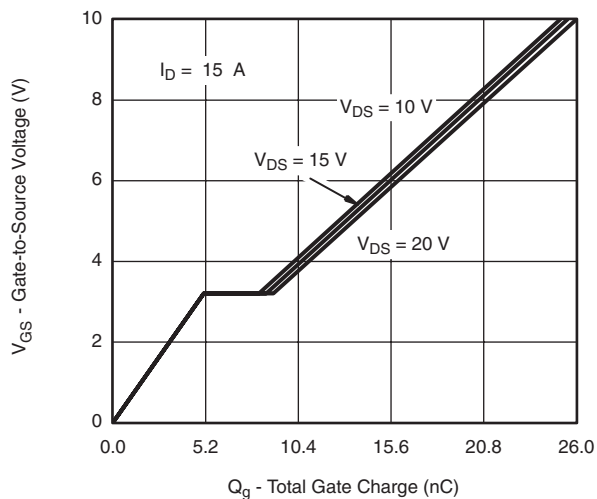
Transfer Characteristics



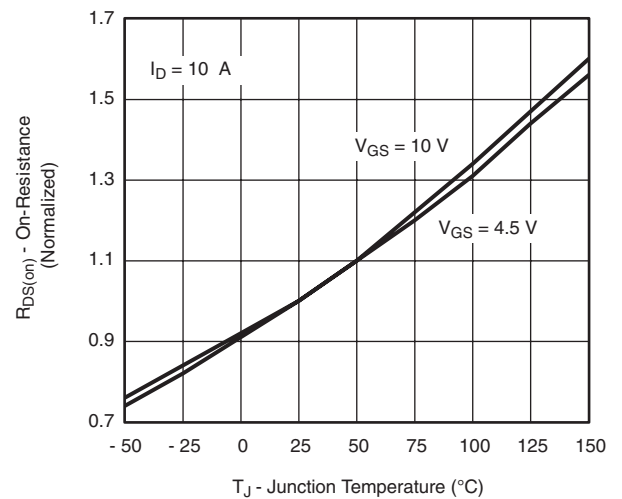
On-Resistance vs. Drain Current



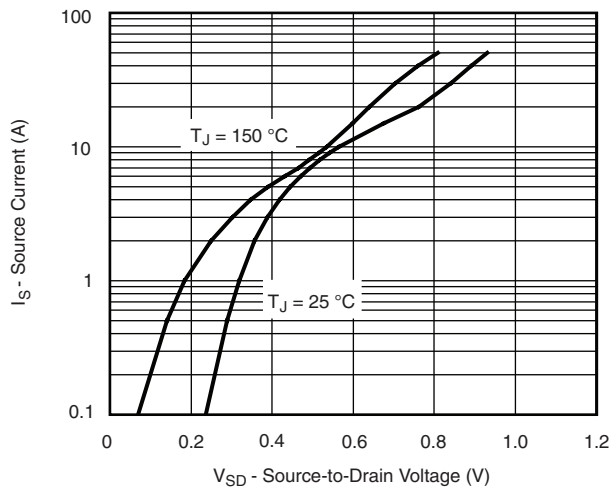
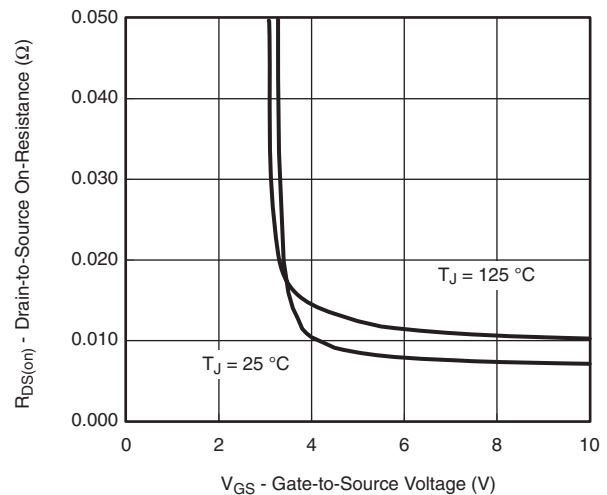
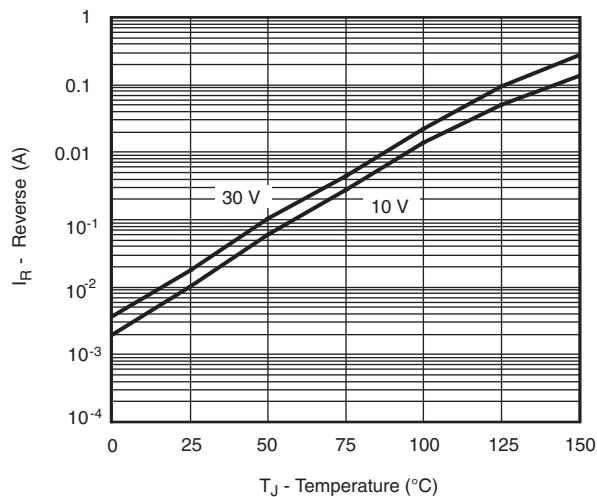
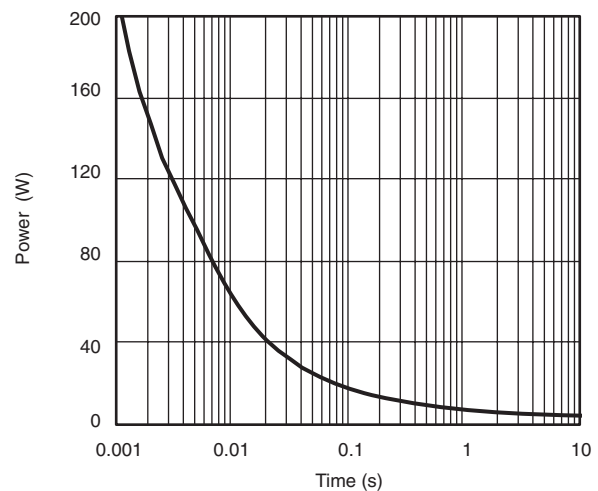
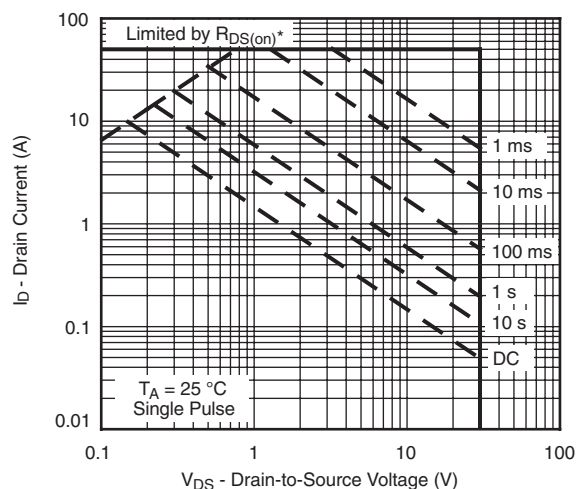
Capacitance



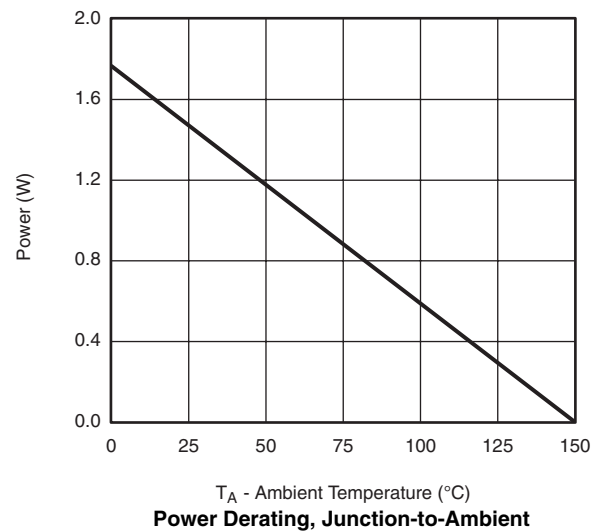
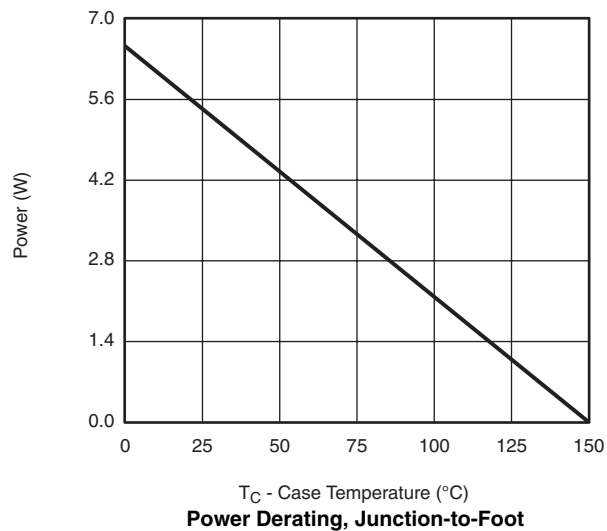
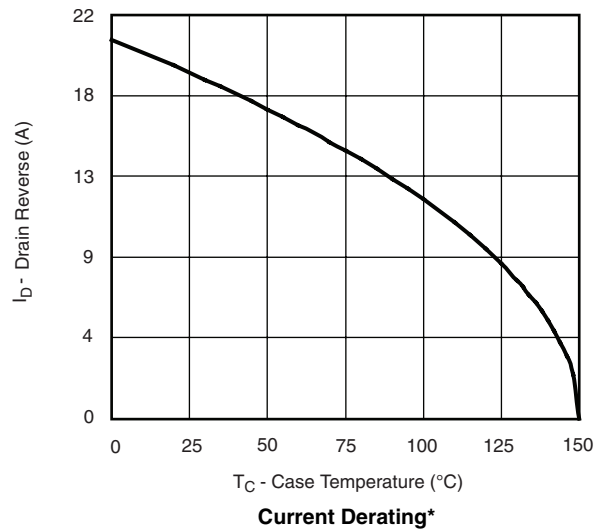
Gate Charge



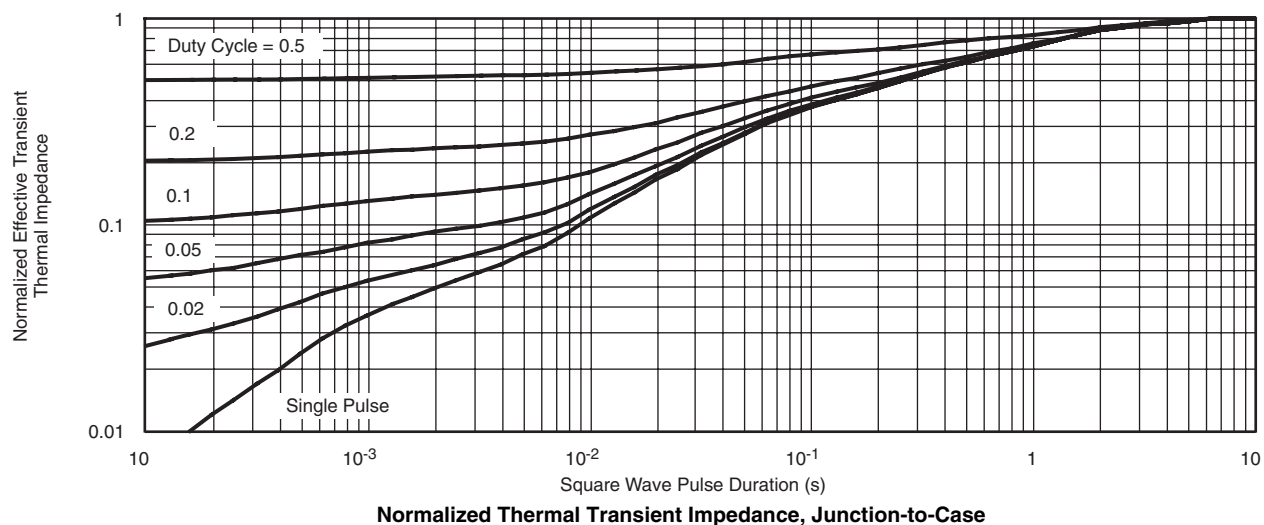
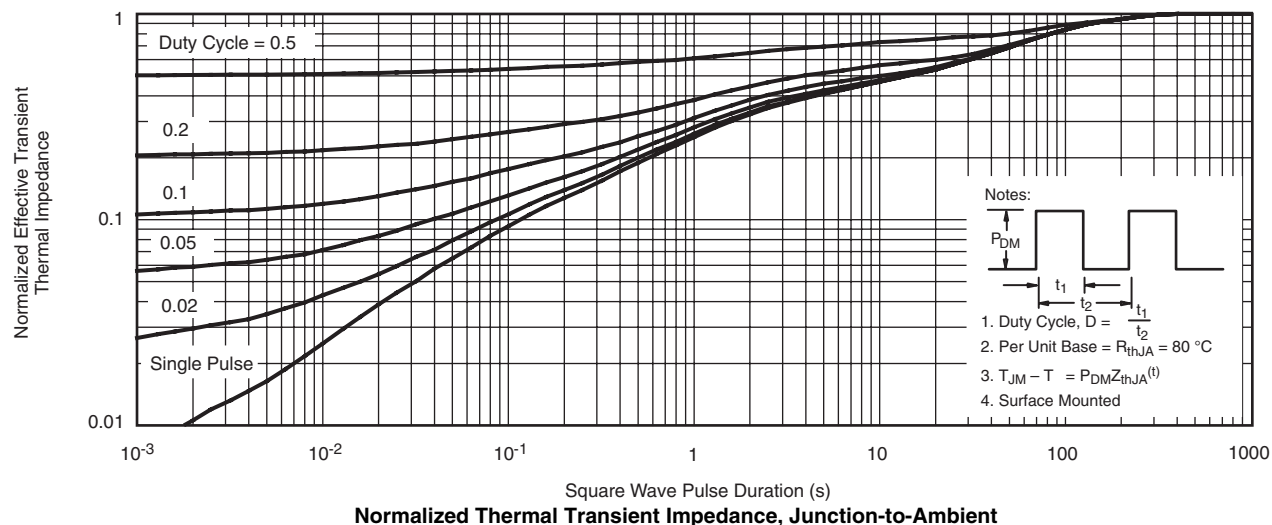
On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Reverse Current (Schottky)****Junction-to-Ambient*** V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified**Safe Operating Area**

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

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